

Wednesday, September 20													
9:15-12:00 Opening Session/Award Ceremony/Plenary Session (Conference Building Main Hall)													
Lunch													
Conference Building 1F Meeting Room 1	Conference Building 1F Meeting Room 2	Conference Building 1F Meeting Room 3	Conference Building 2F HAGI	Conference Building 2F TACHIBANA	Conference Building 2F Meeting Room 4	Conference Building 2F Meeting Room 5	Conference Building 3F Meeting Room 6	Conference Building 3F Meeting Room 7	Conference Building 3F Meeting Room 8	Exhibition Building Meeting Room 1	Exhibition Building Meeting Room 2	Exhibition Building Meeting Room 3	Exhibition Building Meeting Room 4
13:30-15:15 Area7&12 A-1:Magneto-Optical Devices	13:30-15:15 B-1:Organic Devices	13:30-15:15 C-1:Si-based Solar Cells and Modules	13:30-15:00 D-1:ReRAM Technology	13:30-15:15 E-1:Reliability	13:30-15:05 Area5&11 F-1:Advanced Materials & Measurement Circuits for Bio and Medical Applications		13:30-15:15 Area2&13 H-1:Nanocarbon Interconnects and Applications	13:30-15:15 J-1:Oxide based Materials	13:30-15:20 K-1:Interface Engineering		13:30-15:15 Area4&9 M-1:Quantum vs Classical	13:30-15:15 N-1:High-Speed and High-Frequency Devices	13:30-15:15 O-1:SiC Power Devices and Related Technologies
Coffee Break													
15:40-17:25 A-2:Spintronics	15:40-17:25 B-2:Organic Transistors	15:40-16:40 C-2:Compound Semiconductor Solar Cells	15:40-17:30 D-2:Flash Memory	15:40-17:30 Area1&3 E-2:Advanced Transistor Technology	15:40-17:10 F-2:Bio and Micro Systems	15:40-17:10 G-2:GaN Photonic Devices	15:40-17:50 H-2:MEMS & Sensors	15:40-17:25 J-2:2D Materials and Devices	15:40-17:15 K-2:Advanced Power Converters and Packaging Technologies		15:40-17:25 Area4&9 M-2:Non von Neumann Computing I	15:40-17:25 Area6&8&14 N-2:Advanced Growth of Widegap Semiconductors	
19:00-21:00 Banquet (The Westin Sendai)													
Thursday, September 21													
Conference Building 1F Meeting Room 1	Conference Building 1F Meeting Room 2	Conference Building 1F Meeting Room 3	Conference Building 2F HAGI	Conference Building 2F TACHIBANA	Conference Building 2F Meeting Room 4	Conference Building 2F Meeting Room 5	Conference Building 3F Meeting Room 6	Conference Building 3F Meeting Room 7	Conference Building 3F Meeting Room 8	Exhibition Building Meeting Room 1	Exhibition Building Meeting Room 2	Exhibition Building Meeting Room 3	Exhibition Building Meeting Room 4
	9:30-11:15 B-3:Fabrication and Characterization	9:30-10:30 C-3:III-V Photovoltaics	9:30-11:10 Area4&5&9&12 D-3:Non von Neumann Computing II	9:30-11:00 E-3:TFETs	9:30-11:00 F-3:Bio-sensors & Materials	9:30-11:15 G-3:Novel Photonic Devices	9:30-11:20 H-3:Bump Interconnect	9:30-11:15 J-3:2D Materials and Devices II	9:30-11:25 K-3:Ge MOS		9:30-11:00 M-3:Group IV Materials	9:30-11:00 N-3:GaN Device Technologies I	9:30-11:00 O-3:Ga <sub>2</sub> O <sub>3</sub> and Diamond Power Devices
Coffee Break													
11:30-12:30 Short Presentation Area12	11:30-12:30 Short Presentation Area10	11:30-12:30 Short Presentation Area15	11:30-12:30 Short Presentation Area4 Short Presentation Area5	11:30-12:30 Short Presentation Area3	11:30-12:30 Short Presentation Area11	11:30-12:30 Short Presentation Area7	11:30-12:30 Short Presentation Area2 Short Presentation Area9	11:30-12:30 Short Presentation Area13	11:30-12:30 Short Presentation Area1		11:30-12:30 Short Presentation Area8	11:30-12:30 Short Presentation Area6	11:30-12:30 Short Presentation Area14
Lunch													
	14:00-15:00 Area7&10 B-4:Nano and Molecular Photonics		14:00-15:15 Area4&5&9&12 D-4:Non von Neumann Computing III	14:00-15:00 E-4:Negative-Capacitance Transistors	14:00-15:15 F-4:Bio-MEMS		14:00-15:35 H-4:Bonding Technologies	14:00-15:15 J-4:Low-Dimensional Materials and Devices	14:00-15:30 K-4:Process Technology		14:00-15:15 M-4:Germanium based Semiconductors	14:00-15:15 N-4:GaN Device Technologies II	14:00-15:00 O-4:Silicon Power Devices and Related Technologies
Coffee Break													
15:30-17:30 Poster Session (Exhibition Building Exhibition Hall 1, 2)													
17:45-19:15 Rump Sessions (Conference Building 2F HAGI, TACHIBANA)													
Friday, September 22													
Conference Building 1F Meeting Room 1	Conference Building 1F Meeting Room 2	Conference Building 1F Meeting Room 3	Conference Building 2F HAGI	Conference Building 2F TACHIBANA	Conference Building 2F Meeting Room 4	Conference Building 2F Meeting Room 5	Conference Building 3F Meeting Room 6	Conference Building 3F Meeting Room 7	Conference Building 3F Meeting Room 8	Exhibition Building Meeting Room 1	Exhibition Building Meeting Room 2	Exhibition Building Meeting Room 3	Exhibition Building Meeting Room 4
9:30-11:10 Area4&12 A-5:Nonvolatile Memory and Storage Devices	9:30-10:45 Area10&15 B-5:Quantum Dot/Organic Solar Cells	9:30-10:45 C-5:Silicon Photonics I		9:30-10:50 E-5:Steep Slope Transistor and Device Physics	9:30-10:30 F-5:Nano Devices for Chemical & Biosensing	9:30-10:40 G-5:Advanced Imager and Characterization	9:30-11:00 H-5:TSV & 3D Integration	9:30-10:45 J-5:Advanced Functional Nanowire Devices	9:30-10:55 K-5:Ferroelectric Material		9:30-10:45 M-5:Nanostructures: Synthesis and Properties	9:30-10:45 Area6&14 N-5:Advanced Power Device Technologies I	
Coffee Break													
11:15-12:15 Area4&12 A-6:Novel Memory	11:15-12:30 B-6:Perovskite Solar Cells	11:15-12:30 C-6:Quantum Transport		11:15-12:25 E-6:3D Technology	11:15-12:30 Area10&11 F-6:Organic and Bio Devices	11:15-12:25 G-6:Advanced Computing and Memories for Smart Data Processing	11:15-12:30 Area2&7 H-6:Optical Interconnects and Sensors	11:15-12:30 J-6:Characterization & Properties of Nanowires	11:15-12:15 K-6:Theory and Modeling			11:15-12:30 Area6&14 N-6:Advanced Power Device Technologies II	
Lunch													
13:40-15:00 A-7:ReRAM Applications		13:40-14:55 C-7:Quantum Optoelectronics				13:40-14:50 G-7:Advanced Sensing and Connectivity	13:40-14:55 H-7:Silicon Photonics II	13:40-14:40 J-7: TBC	13:40-14:55 K-7:Magnetic Tunnel Junctions			13:40-14:55 N-7:Compound Semiconductor Device & Process	
Coffee Break													
15:10-16:55 A-8:PCRAM						15:10-16:20 G-8:Advanced MEMS Sensors and Analog Front End	15:10-16:25 H-8:Silicon Photonics III		15:10-16:25 K-8:Spintronics Devices				

Area Scope	Area 1: Advanced LSI Processing & Materials Science
	Area 2: Interconnect Technologies and 3D Integration/ Sensor/ MEMS Integration/ Materials and Characterization
	Area 3: CMOS Devices / Device Physics
	Area 4: Advanced Memory Technology
	Area 5: Advanced Circuits and Systems
	Area 6: Compound Semiconductor Electron Devices & Related Technologies
	Area 7: Photonic Devices and Related Technologies
	Area 8: Advanced Material Synthesis and Crystal Growth Technology

Area Scope	Area 9: Physics and Applications of Novel Functional Devices and Materials
	Area 10: Organic Materials Science, Device Physics, Applications and Printed Technologies
	Area 11: Sensors and Materials for Biology, Chemistry and Medicine
	Area 12: Spintronics Materials and Devices
	Area 13: Applications of Nanotubes, Nanowires, and Graphene and related 2D materials
	Area 14: Power Devices and Materials
	Area 15: Photovoltaic Materials and Devices